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#### Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

#### **Applications of Embedded - FPGAs**

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Active
Number of LABs/CLBs	
Number of Logic Elements/Cells	
Total RAM Bits	516096
Number of I/O	147
Number of Gates	300000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1a3pe3000l-pqg208i

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

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FPGA Array Architecture in Low Power Flash Devices

## **Array Coordinates**

During many place-and-route operations in the Microsemi Designer software tool, it is possible to set constraints that require array coordinates. Table 1-2 provides array coordinates of core cells and memory blocks for IGLOO and ProASIC3 devices. Table 1-3 provides the information for IGLOO PLUS devices. Table 1-4 on page 17 provides the information for IGLOO nano and ProASIC3 nano devices. The array coordinates are measured from the lower left (0, 0). They can be used in region constraints for specific logic groups/blocks, designated by a wildcard, and can contain core cells, memories, and I/Os.

I/O and cell coordinates are used for placement constraints. Two coordinate systems are needed because there is not a one-to-one correspondence between I/O cells and core cells. In addition, the I/O coordinate system changes depending on the die/package combination. It is not listed in Table 1-2. The Designer ChipPlanner tool provides the array coordinates of all I/O locations. I/O and cell coordinates are used for placement constraints. However, I/O placement is easier by package pin assignment.

Figure 1-9 on page 17 illustrates the array coordinates of a 600 k gate device. For more information on how to use array coordinates for region/placement constraints, see the *Designer User's Guide* or online help (available in the software) for software tools.

		Vers	aTiles		Memor	y Rows	Entire Die		
Device	Min.		Max.		Bottom	Тор	Min.	Max.	
IGLOO	ProASIC3/ ProASIC3L	x	у	x	у	(x, y)	(x, y)	(x, y)	(x, y)
AGL015	A3P015	3	2	34	13	None	None	(0, 0)	(37, 15)
AGL030	A3P030	3	3	66	13	None	None	(0, 0)	(69, 15)
AGL060	A3P060	3	2	66	25	None	(3, 26)	(0, 0)	(69, 29)
AGL125	A3P125	3	2	130	25	None	(3, 26)	(0, 0)	(133, 29)
AGL250	A3P250/L	3	2	130	49	None	(3, 50)	(0, 0)	(133, 53)
AGL400	A3P400	3	2	194	49	None	(3, 50)	(0, 0)	(197, 53)
AGL600	A3P600/L	3	4	194	75	(3, 2)	(3, 76)	(0, 0)	(197, 79)
AGL1000	A3P1000/L	3	4	258	99	(3, 2)	(3, 100)	(0, 0)	(261, 103)
AGLE600	A3PE600/L, RT3PE600L	3	4	194	75	(3, 2)	(3, 76)	(0, 0)	(197, 79)
	A3PE1500	3	4	322	123	(3, 2)	(3, 124)	(0, 0)	(325, 127)
AGLE3000	A3PE3000/L, RT3PE3000L	3	6	450	173	(3, 2) or (3, 4)	(3, 174) or (3, 176)	(0, 0)	(453, 179)

#### Table 1-2 • IGLOO and ProASIC3 Array Coordinates

#### Table 1-3 • IGLOO PLUS Array Coordinates

		Vers	aTiles		Memor	y Rows	Entire Die		
Device	Min.		Ма	Max. Bottom		Тор	Min.	Max.	
IGLOO PLUS	PLUS X Y X Y		(x, y)	(x, y)	(x, y)	(x, y)			
AGLP030	2	3	67	13	None	None	(0, 0)	(69, 15)	
AGLP060	2	2	67	25	None	(3, 26)	(0, 0)	(69, 29)	
AGLP125	2	2	131	25	None	(3, 26)	(0, 0)	(133, 29)	



*Figure 2-3* • Flash\*Freeze Mode Type 2 – Controlled by Flash\*Freeze Pin and Internal Logic (LSICC signal)



Figure 2-4 • Flash\*Freeze Mode Type 2 – Timing Diagram

I/O Туре	Beginning of I/O Name	Notes						
Single-Ended	GAAO/IOuxwByVz	Only one of the I/Os can be directly connected to a						
	GAA1/IOuxwByVz	quadrant global at a time						
	GAA2/IOuxwByVz							
	GABO/IOuxwByVz	Only one of the I/Os can be directly connected to a						
	GAB1/IOuxwByVz	quadrant global at a time.						
	GAB2/IOuxwByVz							
	GAC0/IOuxwByVz	Only one of the I/Os can be directly connected to a						
	GAC1/IOuxwByVz	quadrant global at a time.						
	GAC2/IOuxwByVz							
	GBAO/IOuxwByVz	Only one of the I/Os can be directly connected to a global						
	GBA1/IOuxwByVz	at a time.						
	GBA2/IOuxwByVz							
	GBBO/IOuxwByVz	Only one of the I/Os can be directly connected to a global						
	GBB1/IOuxwByVz	at a time.						
	GBB2/IOuxwByVz							
	GBC0/IOuxwByVz	Only one of the I/Os can be directly connected to a glob						
	GBC1/IOuxwByVz	at a time.						
	GBC2/IOuxwByVz							
	GDAO/IOuxwByVz	Only one of the I/Os can be directly connected to a glob						
	GDA1/IOuxwByVz	at a time.						
	GDA2/IOuxwByVz							
	GDBO/IOuxwByVz	Only one of the I/Os can be directly connected to a globa						
	GDB1/IOuxwByVz	at a time.						
	GDB2/IOuxwByVz							
	GDC0/IOuxwByVz	Only one of the I/Os can be directly connected to a global						
	GDC1/IOuxwByVz	at a time.						
	GDC2/IOuxwByVz							
	GEAO/IOuxwByVz	Only one of the I/Os can be directly connected to a global						
	GEA1/IOuxwByVz	at a time.						
	GEA2/IOuxwByVz							
	GEBO/IOuxwByVz	Only one of the I/Os can be directly connected to a global						
	GEB1/IOuxwByVz	at a time.						
	GEB2/IOuxwByVz							
	GEC0/IOuxwByVz	Only one of the I/Os can be directly connected to a global						
	GEC1/IOuxwByVz	at a time.						
	GEC2/IOuxwByVz							

#### Table 3-3 • Quadrant Global Pin Name

Note: Only one of the I/Os can be directly connected to a quadrant at a time.

## Spine Access

The physical location of each spine is identified by the letter T (top) or B (bottom) and an accompanying number (T*n* or B*n*). The number *n* indicates the horizontal location of the spine; 1 refers to the first spine on the left side of the die. Since there are six chip spines in each spine tree, there are up to six spines available for each combination of T (or B) and *n* (for example, six T1 spines). Similarly, there are three quadrant spines available for each combination of T (or B) and *n* (for example, four T1 spines), as shown in Figure 3-7.



Figure 3-7 • Chip Global Aggregation

A spine is also called a local clock network, and is accessed by the dedicated global MUX architecture. These MUXes define how a particular spine is driven. Refer to Figure 3-8 on page 60 for the global MUX architecture. The MUXes for each chip global spine are located in the middle of the die. Access to the top and bottom chip global spine is available from the middle of the die. There is no control dependency between the top and bottom spines. If a top spine, T1, of a chip global network is assigned to a net, B1 is not wasted and can be used by the global clock network. The signal assigned only to the top or bottom spine cannot access the middle two rows of the architecture. However, if a spine is using the top and bottom at the same time (T1 and B1, for instance), the previous restriction is lifted.

The MUXes for each quadrant global spine are located in the north and south sides of the die. Access to the top and bottom quadrant global spines is available from the north and south sides of the die. Since the MUXes for quadrant spines are located in the north and south sides of the die, you should not try to drive T1 and B1 quadrant spines from the same signal.

ProASIC3L FPGA Fabric User's Guide



Note: OAVDIVRST exists only in the Fusion PLL.

#### Figure 3-15 • PLLs in Low Power Flash Devices

You can use the syn\_global\_buffers attribute in Synplify to specify a maximum number of global macros to be inserted in the netlist. This can also be used to restrict the number of global buffers inserted. In the Synplicity 8.1 version or newer, a new attribute, syn\_global\_minfanout, has been added for low power flash devices. This enables you to promote only the high-fanout signal to global. However, be aware that you can only have six signals assigned to chip global networks, and the rest of the global signals should be assigned to quadrant global networks. So, if the netlist has 18 global macros, the remaining 12 global macros should have fanout that allows the instances driven by these globals to be placed inside a quadrant.

### **Global Promotion and Demotion Using PDC**

The HDL source file or schematic is the preferred place for defining which signals should be assigned to a clock network using clock macro instantiation. This method is preferred because it is guaranteed to be honored by the synthesis tools and Designer software and stop any replication on this net by the synthesis tool. Note that a signal with fanout may have logic replication if it is not promoted to global during synthesis. In that case, the user cannot promote that signal to global using PDC. See Synplicity Help for details on using this attribute. To help you with global management, Designer allows you to promote a signal to a global network or demote a global macro to a regular macro from the user netlist using the compile options and/or PDC commands.

The following are the PDC constraints you can use to promote a signal to a global network:

1. PDC syntax to promote a regular net to a chip global clock:

assign\_global\_clock -net netname

The following will happen during promotion of a regular signal to a global network:

- If the net is external, the net will be driven by a CLKINT inserted automatically by Compile.
- The I/O macro will not be changed to CLKBUF macros.
- If the net is an internal net, the net will be driven by a CLKINT inserted automatically by Compile.
- 2. PDC syntax to promote a net to a quadrant clock:

assign\_local\_clock -net netname -type quadrant UR|UL|LR|LL

This follows the same rule as the chip global clock network.

The following PDC command demotes the clock nets to regular nets.

unassign\_global\_clock -net netname

Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs







Figure 4-10 • Illustration of Hardwired I/O (global input pins) Usage for IGLOO and ProASIC3 devices 30 k Gates and Smaller

difference will cause the VCO to increase its frequency until the output signal is phase-identical to the input after undergoing division. In other words, lock in both frequency and phase is achieved when the output frequency is M times the input. Thus, clock division in the feedback path results in multiplication at the output.

A similar argument can be made when the delay element is inserted into the feedback path. To achieve steady-state lock, the VCO output signal will be delayed by the input period *less* the feedback delay. For periodic signals, this is equivalent to time-advancing the output clock by the feedback delay.

Another key parameter of a PLL system is the acquisition time. Acquisition time is the amount of time it takes for the PLL to achieve lock (i.e., phase-align the feedback signal with the input reference clock). For example, suppose there is no voltage applied to the VCO, allowing it to operate at its free-running frequency. Should an input reference clock suddenly appear, a lock would be established within the maximum acquisition time.

# **Functional Description**

This section provides detailed descriptions of PLL block functionality: clock dividers and multipliers, clock delay adjustment, phase adjustment, and dynamic PLL configuration.

## **Clock Dividers and Multipliers**

The PLL block contains five programmable dividers. Figure 4-20 shows a simplified PLL block.



Figure 4-20 • PLL Block Diagram

## **SRAM Features**

### RAM4K9 Macro

RAM4K9 is the dual-port configuration of the RAM block (Figure 6-4). The RAM4K9 nomenclature refers to both the deepest possible configuration and the widest possible configuration the dual-port RAM block can assume, and does not denote a possible memory aspect ratio. The RAM block can be configured to the following aspect ratios: 4,096×1, 2,048×2, 1,024×4, and 512×9. RAM4K9 is fully synchronous and has the following features:

- Two ports that allow fully independent reads and writes at different frequencies
- Selectable pipelined or nonpipelined read
- Active-low block enables for each port
- Toggle control between read and write mode for each port
- · Active-low asynchronous reset
- Pass-through write data or hold existing data on output. In pass-through mode, the data written to the write port will immediately appear on the read port.
- Designer software will automatically facilitate falling-edge clocks by bubble-pushing the inversion to previous stages.



*Note:* For timing diagrams of the RAM signals, refer to the appropriate family datasheet. *Figure 6-4* • RAM4K9 Simplified Configuration

### Signal Descriptions for RAM4K9

Note: Automotive ProASIC3 devices support single-port SRAM capabilities, or dual-port SRAM only under specific conditions. Dual-port mode is supported if the clocks to the two SRAM ports are the same and 180° out of phase (i.e., the port A clock is the inverse of the port B clock). Since Libero SoC macro libraries support a dual-port macro only, certain modifications must be made. These are detailed below.

The following signals are used to configure the RAM4K9 memory element:

#### WIDTHA and WIDTHB

These signals enable the RAM to be configured in one of four allowable aspect ratios (Table 6-2 on page 154).

Note: When using the SRAM in single-port mode for Automotive ProASIC3 devices, WIDTHB should be tied to ground.

### IGLOO and ProASIC3

For boards and cards with three levels of staging, card power supplies must have time to reach their final values before the I/Os are connected. Pay attention to the sizing of power supply decoupling capacitors on the card to ensure that the power supplies are not overloaded with capacitance.

Cards with three levels of staging should have the following sequence:

- Grounds
- Powers
- I/Os and other pins

For Level 3 and Level 4 compliance with the 30K gate device, cards with two levels of staging should have the following sequence:

- Grounds
- Powers, I/Os, and other pins

## **Cold-Sparing Support**

*Cold-sparing* refers to the ability of a device to leave system data undisturbed when the system is powered up, while the component itself is powered down, or when power supplies are floating.

The resistor value is calculated based on the decoupling capacitance on a given power supply. The RC constant should be greater than 3  $\mu$ s.

To remove resistor current during operation, it is suggested that the resistor be disconnected (e.g., with an NMOS switch) from the power supply after the supply has reached its final value. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" section on page 373 for details on cold-sparing.

Cold-sparing means that a subsystem with no power applied (usually a circuit board) is electrically connected to the system that is in operation. This means that all input buffers of the subsystem must present very high input impedance with no power applied so as not to disturb the operating portion of the system.

The 30 k gate devices fully support cold-sparing, since the I/O clamp diode is always off (see Table 7-12 on page 193). If the 30 k gate device is used in applications requiring cold-sparing, a discharge path from the power supply to ground should be provided. This can be done with a discharge resistor or a switched resistor. This is necessary because the 30K gate devices do not have built-in I/O clamp diodes.

For other IGLOO and ProASIC3 devices, since the I/O clamp diode is always active, cold-sparing can be accomplished either by employing a bus switch to isolate the device I/Os from the rest of the system or by driving each I/O pin to 0 V. If the resistor is chosen, the resistor value must be calculated based on decoupling capacitance on a given power supply on the board (this decoupling capacitance is in parallel with the resistor). The RC time constant should ensure full discharge of supplies before cold-sparing functionality is required. The resistor is necessary to ensure that the power pins are discharged to ground every time there is an interruption of power to the device.

IGLOOe and ProASIC3E devices support cold-sparing for all I/O configurations. Standards, such as PCI, that require I/O clamp diodes can also achieve cold-sparing compliance, since clamp diodes get disconnected internally when the supplies are at 0 V.

When targeting low power applications, I/O cold-sparing may add additional current if a pin is configured with either a pull-up or pull-down resistor and driven in the opposite direction. A small static current is induced on each I/O pin when the pin is driven to a voltage opposite to the weak pull resistor. The current is equal to the voltage drop across the input pin divided by the pull resistor. Refer to the "Detailed I/O DC Characteristics" section of the appropriate family datasheet for the specific pull resistor value for the corresponding I/O standard.

For example, assuming an LVTTL 3.3 V input pin is configured with a weak pull-up resistor, a current will flow through the pull-up resistor if the input pin is driven LOW. For LVTTL 3.3 V, the pull-up resistor is ~45 k $\Omega$ , and the resulting current is equal to 3.3 V / 45 k $\Omega$  = 73 µA for the I/O pin. This is true also when a weak pull-down is chosen and the input pin is driven HIGH. This current can be avoided by driving the input LOW when a weak pull-down resistor is used and driving it HIGH when a weak pull-up resistor is used.

This current draw can occur in the following cases:



I/O Structures in IGLOO and ProASIC3 Devices





At the system level, the skew circuit can be used in applications where transmission activities on bidirectional data lines need to be coordinated. This circuit, when selected, provides a timing margin that can prevent bus contention and subsequent data loss and/or transmitter over-stress due to transmitter-to-transmitter current shorts. Figure 7-16 presents an example of the skew circuit implementation in a bidirectional communication system. Figure 7-17 on page 201 shows how bus contention is created, and Figure 7-18 on page 201 shows how it can be avoided with the skew circuit.



Figure 7-16 • Example of Implementation of Skew Circuits in Bidirectional Transmission Systems Using IGLOO or ProASIC3 Devices

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Figure 7-18 • Timing Diagram (with skew circuit selected)



I/O Structures in IGLOOe and ProASIC3E Devices

### 5 V Output Tolerance

IGLOO and ProASIC3 I/Os must be set to 3.3 V LVTTL or 3.3 V LVCMOS mode to reliably drive 5 V TTL receivers. It is also critical that there be NO external I/O pull-up resistor to 5 V, since this resistor would pull the I/O pad voltage beyond the 3.6 V absolute maximum value and consequently cause damage to the I/O.

When set to 3.3 V LVTTL or 3.3 V LVCMOS mode, the I/Os can directly drive signals into 5 V TTL receivers. In fact, VOL = 0.4 V and VOH = 2.4 V in both 3.3 V LVTTL and 3.3 V LVCMOS modes exceeds the VIL = 0.8 V and VIH = 2 V level requirements of 5 V TTL receivers. Therefore, level 1 and level 0 will be recognized correctly by 5 V TTL receivers.

## **Schmitt Trigger**

A Schmitt trigger is a buffer used to convert a slow or noisy input signal into a clean one before passing it to the FPGA. Using Schmitt trigger buffers guarantees a fast, noise-free input signal to the FPGA.

ProASIC3E devices have Schmitt triggers built into their I/O circuitry. The Schmitt trigger is available for the LVTTL, LVCMOS, and 3.3 V PCI I/O standards.

This feature can be implemented by using a Physical Design Constraints (PDC) command (Table 8-6 on page 218) or by selecting a check box in the I/O Attribute Editor in Designer. The check box is cleared by default.

## Selectable Skew between Output Buffer Enable and Disable Times

Low power flash devices have a configurable skew block in the output buffer circuitry that can be enabled to delay output buffer assertion without affecting deassertion time. Since this skew block is only available for the OE signal, the feature can be used in tristate and bidirectional buffers. A typical 1.2 ns delay is added to the OE signal to prevent potential bus contention. Refer to the appropriate family datasheet for detailed timing diagrams and descriptions.

The Skew feature is available for all I/O standards.

This feature can be implemented by using a PDC command (Table 8-6 on page 218) or by selecting a check box in the I/O Attribute Editor in Designer. The check box is cleared by default.

The configurable skew block is used to delay output buffer assertion (enable) without affecting deassertion (disable) time.





I/O Software Control in Low Power Flash Devices

# Implementing I/Os in Microsemi Software

Microsemi Libero SoC software is integrated with design entry tools such as the SmartGen macro builder, the ViewDraw schematic entry tool, and an HDL editor. It is also integrated with the synthesis and Designer tools. In this section, all necessary steps to implement the I/Os are discussed.

## **Design Entry**

There are three ways to implement I/Os in a design:

- 1. Use the SmartGen macro builder to configure I/Os by generating specific I/O library macros and then instantiating them in top-level code. This is especially useful when creating I/O bus structures.
- 2. Use an I/O buffer cell in a schematic design.
- 3. Manually instantiate specific I/O macros in the top-level code.

If technology-specific macros, such as INBUF\_LVCMOS33 and OUTBUF\_PCI, are used in the HDL code or schematic, the user will not be able to change the I/O standard later on in Designer. If generic I/O macros are used, such as INBUF, OUTBUF, TRIBUF, CLKBUF, and BIBUF, the user can change the I/O standard using the Designer I/O Attribute Editor tool.

### Using SmartGen for I/O Configuration

The SmartGen tool in Libero SoC provides a GUI-based method of configuring the I/O attributes. The user can select certain I/O attributes while configuring the I/O macro in SmartGen. The steps to configure an I/O macro with specific I/O attributes are as follows:

- 1. Open Libero SoC.
- 2. On the left-hand side of the Catalog View, select I/O, as shown in Figure 9-2.

Figure 9-2 • SmartGen Catalog

- The I/O standard of technology-specific I/O macros cannot be changed in the I/O Attribute Editor (see Figure 9-6).
- The user MUST instantiate differential I/O macros (LVDS/LVPECL) in the design. This is the only way to use these standards in the design (IGLOO nano and ProASIC3 nano devices do not support differential inputs).
- To implement the DDR I/O function, the user must instantiate a DDR\_REG or DDR\_OUT macro. This is the only way to use a DDR macro in the design.

Figure 9-6 • Assigning a Different I/O Standard to the Generic I/O Macro

### Performing Place-and-Route on the Design

The netlist created by the synthesis tool should now be imported into Designer and compiled. During Compile, the user can specify the I/O placement and attributes by importing the PDC file. The user can also specify the I/O placement and attributes using ChipPlanner and the I/O Attribute Editor under MVN.

### Defining I/O Assignments in the PDC File

A PDC file is a Tcl script file specifying physical constraints. This file can be imported to and exported from Designer.

Table 9-3 shows I/O assignment constraints supported in the PDC file.

Command	Action	Example	Comment									
I/O Banks Setting	I/O Banks Setting Constraints											
set_iobank	Sets the I/O supply voltage, $V_{CCI}$ , and the input reference voltage, $V_{REF}$ , for the specified I/O bank.	<pre>set_iobank bankname [-vcci vcci_voltage] [-vref vref_voltage] set_iobank Bank7 -vcci 1.50 -vref 0.75</pre>	Must use in case of mixed I/O voltage (V <sub>CCI</sub> ) design									
set_vref	Assigns a V <sub>REF</sub> pin to a bank.	set_vref -bank [bankname] [pinnum] set_vref -bank Bank0 685 704 723 742 761	Must use if voltage- referenced I/Os are used									
set_vref_defaults	Sets the default $V_{REF}$ pins for the specified bank. This command is ignored if the bank does not need a $V_{REF}$ pin.	set_vref_defaults bankname set_vref_defaults bank2										

Table 9-3 • PDC I/O Constraints

*Note: Refer to the* Libero SoC User's Guide for detailed rules on PDC naming and syntax conventions.

# **FlashROM and Programming Files**

Each low power flash device has 1 kbit of on-chip, nonvolatile flash memory that can be accessed from the FPGA core. This nonvolatile FlashROM is arranged in eight pages of 128 bits (Figure 13-3). Each page can be programmed independently, with or without the 128-bit AES encryption. The FlashROM can only be programmed via the IEEE 1532 JTAG port and cannot be programmed from the FPGA core. In addition, during programming of the FlashROM, the FPGA core is powered down automatically by the on-chip programming control logic.

			Byte Number in Page														
		15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
	7																
	6																
be	5																
L m	4																
Z Ø	3																
ag	2																
₽.	1																
	0																

#### Figure 13-3 • FlashROM Architecture

When using FlashROM combined with AES, many subscription-based applications or device serialization applications are possible. The FROM configurator found in the Libero SoC Catalog supports easy management of the FlashROM contents, even over large numbers of devices. The FROM configurator can support FlashROM contents that contain the following:

- Static values
- Random numbers
- Values read from a file
- Independent updates of each page

In addition, auto-incrementing of fields is possible. In applications where the FlashROM content is different for each device, you have the option to generate a single STAPL file for all the devices or individual serialization files for each device. For more information on how to generate the FlashROM content for device serialization, refer to the "FlashROM in Microsemi's Low Power Flash Devices" section on page 133.

Libero SoC includes a unique tool to support the generation and management of FlashROM and FPGA programming files. This tool is called FlashPoint.

Depending on the applications, designers can use the FlashPoint software to generate a STAPL file with different contents. In each case, optional AES encryption and/or different security settings can be set.

In Designer, when you click the Programming File icon, FlashPoint launches, and you can generate STAPL file(s) with four different cases (Figure 13-4 on page 334). When the serialization feature is used during the configuration of FlashROM, you can generate a single STAPL file that will program all the devices or an individual STAPL file for each device.

The following cases present the FPGA core and FlashROM programming file combinations that can be used for different applications. In each case, you can set the optional security settings (FlashLock Pass Key and/or AES Key) depending on the application.

- 1. A single STAPL file or multiple STAPL files with multiple FlashROM contents and the FPGA core content. A single STAPL file will be generated if the device serialization feature is not used. You can program the whole FlashROM or selectively program individual pages.
- 2. A single STAPL file for the FPGA core content

Boundary Scan in Low Power Flash Devices

# **Microsemi's Flash Devices Support the JTAG Feature**

The flash-based FPGAs listed in Table 16-1 support the JTAG feature and the functions described in this document.

#### Table 16-1 • Flash-Based FPGAs

Series	Family <sup>*</sup>	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC <sup>®</sup> 3 FPGA fabric, programmable analog block, support for ARM <sup>®</sup> Cortex <sup>™</sup> -M1 soft processors, and flash memory into a monolithic device

Note: \*The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

### IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 16-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

### ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 16-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.

## **SRAM** Initialization

Users can also initialize embedded SRAMs of the low power flash devices. The initialization of the embedded SRAM blocks of the design can be done using UJTAG tiles, where the initialization data is imported using the TAP Controller. Similar functionality is available in ProASIC<sup>PLUS</sup> devices using JTAG. The guidelines for implementation and design examples are given in the *RAM Initialization and ROM Emulation in ProASIC<sup>PLUS</sup> Devices* application note.

SRAMs are volatile by nature; data is lost in the absence of power. Therefore, the initialization process should be done at each power-up if necessary.

## FlashROM Read-Back Using JTAG

The low power flash architecture contains a dedicated nonvolatile FlashROM block, which is formatted into eight 128-bit pages. For more information on FlashROM, refer to the "FlashROM in Microsemi's Low Power Flash Devices" section on page 133. The contents of FlashROM are available to the VersaTiles during normal operation through a read operation. As a result, the UJTAG macro can be used to provide the FlashROM contents to the JTAG port during normal operation. Figure 17-7 illustrates a simple block diagram of using UJTAG to read the contents of FlashROM during normal operation.

The FlashROM read address can be provided from outside the FPGA through the TDI input or can be generated internally using the core logic. In either case, data serialization logic is required (Figure 17-7) and should be designed using the VersaTile core logic. FlashROM contents are read asynchronously in parallel from the flash memory and shifted out in a synchronous serial format to TDO. Shifting the serial data out of the serialization block should be performed while the TAP is in UDRSH mode. The coordination between TCK and the data shift procedure can be done using the TAP state machine by monitoring UDRSH, UDRCAP, and UDRUPD.



Figure 17-7 • Block Diagram of Using UJTAG to Read FlashROM Contents

Power-Up/-Down Behavior of Low Power Flash Devices

# **Related Documents**

### Datasheets

ProASIC3 Flash Family FPGAs http://www.microsemi.com/soc/documents/PA3\_DS.pdf ProASIC3E Flash Family FPGAs http://www.microsemi.com/soc/documents/PA3E\_DS.pdf

# List of Changes

The following table lists critical changes that were made in each revision of the chapter.

Date	Changes	Page
v1.2 (December 2008)	IGLOO nano and ProASIC3 nano devices were added to the document as supported device types.	
v1.1 (October 2008)	The "Introduction" section was updated to add Military ProASIC3EL and RT ProASIC3 devices to the list of devices that can have inputs driven in while the device is not powered.	373
	The "Flash Devices Support Power-Up Behavior" section was revised to include new families and make the information more concise.	374
	The "Cold-Sparing" section was revised to add Military ProASIC3/EL and RT ProASIC3 devices to the lists of devices with and without cold-sparing support.	382
	The "Hot-Swapping" section was revised to add Military ProASIC3/EL and RT ProASIC3 devices to the lists of devices with and without hot-swap support. AGL400 was added to the list of devices that do not support hot-swapping.	383
v1.0 (August 2008)	This document was revised, renamed, and assigned a new part number. It now includes data for the IGLOO and ProASIC3L families.	N/A
v1.3 (March 2008)	The "List of Changes" section was updated to include the three different I/O Structure handbook chapters.	384
v1.2 (February 2008)	The first sentence of the "PLL Behavior at Brownout Condition" section was updated to read, "When PLL power supply voltage and/or V <sub>CC</sub> levels drop below the VCC brownout levels (0.75 V $\pm$ 0.25 V), the PLL output lock signal goes low and/or the output clock is lost."	381
v1.1 (January 2008)	The "PLL Behavior at Brownout Condition" section was added.	381